

ABSTRACT OF THE DISCLOSURE

A thin film transistor is provided including an active layer, in which a source region and drain region are formed, a first light-shielding film shielding a light incident on the active layer, and a second light-shielding film between the active layer and the first shielding film. A carrier concentration of at least surface portion of the second light-shielding film which opposes the active layer is about $10^{17}/\text{cm}^3$ or less.